HARRIS SEMICONDUCTOR

CA3127

August 1996

High Frequency NPN Transistor Array

Features

- **Gain Bandwidth Product (f_T). . . . . >1GHz**
- **Power Gain . . . . 30dB (Typ) at 100MHz**
- **Noise Figure . . . . 3.5dB (Typ) at 100MHz**
- **Five Independent Transistors on a Common Substrate**

Applications

- **VHF Amplifiers**
- **Multifunction Combinations - RF/Mixer/Oscillator**
- **Sense Amplifiers**
- **Synchronous Detectors**
- **VHF Mixers**
- **IF Converter**
- **IF Amplifiers**
- **Synthesizers**
- **Cascade Amplifiers**

Description

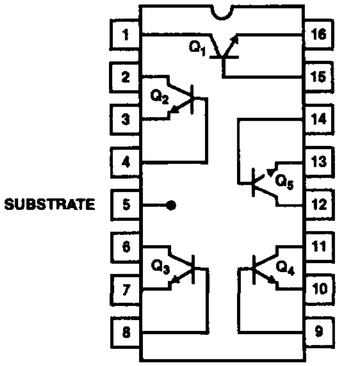
The CA3127 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Each of the completely isolated transistors exhibits low 1/f noise and a value of f_T in excess of 1GHz, making the CA3127 useful from DC to 500MHz. Access is provided to each of the terminals for the individual transistors and a separate substrate connection has been provided for maximum application flexibility. The monolithic construction of the CA3127 provides close electrical and thermal matching of the five transistors.

Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CA3127E	-55 to 125	16 Ld PDIP	E16.3
CA3127M (3127)	-55 to 125	16 Ld SOIC	M16.15
CA3127M96 (3127)	-55 to 125	16 Ld SOIC Tape and Reel	M16.15

Pinout

CA3127
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.